

AMENDMENTS TO THE CLAIMS

1-33. (Canceled)

34. (Currently Amended) A plating method comprising:
preparing a substrate having fine recesses for interconnects covered with a seed layer;
supplying a plating solution between a surface of the seed layer and an anode spaced
from the seed layer at a certain interval through a porous contact member; and
plating the substrate by applying plating voltage between the seed layer and said anode;
wherein said plating is performed while a change of state of the plating voltage that is
applied between the seed layer and the anode occurs that results from intermittence of the plating
voltage, a change of pressing state between said porous contact member and the seed layer
occurs, and the change of state of the plating voltage is correlated with the change of pressing
state between said porous contact member and the seed layerwherein a change of the state of
plating voltage applied between the seed layer and said anode, and a change of pressing state
between said porous contact member and the seed layer are correlated.

35. (Original) A plating method according to claim 34, wherein said change of pressing
state between said porous contact member and the seed layer is a change of pressure between
said porous contact member and the seed layer.

36. (Canceled)

37. (Currently Amended) A plating method according to claim 34, wherein said
change of the state of plating voltage applied between the seed layer and said anode, and said
change of pressing state between said porous contact member and the seed layer, are correlated
by applying said plating voltage when a pressure between said porous contact member and the
surface of the seed layer is increased relativelyrelative to a previous pressure, and by not
applying said plating voltage when a pressure between said porous contact member and the seed
layer is lowered more than the previous timerelativelyrelative to a previous pressure.

38. (Original) A plating method according to claim 34, wherein said change of pressing state between said porous contact member and the seed layer is a change of contact and non-contact between said porous contact member and the surface of the seed layer.

39. (Currently Amended) A plating method according to claim 34, wherein said change of the state of plating voltage applied between the seed layer and said anode, and said change of pressing state between said porous contact member and the seed layer, are correlated so as to synchronize contact between said porous contact member and the surface of the seed layer and application of plating voltage between the seed layer and said anode.

40. (Currently Amended) A plating method according to claim 34, wherein said change of the state of plating voltage applied between the seed layer and said anode, and said change of pressing state between said porous contact member and the seed layer, are correlated so as not to apply plating voltage between the seed layer and said anode when said porous contact member is brought out of contact with the surface of the seed layer, and so as to apply plating voltage between the seed layer and said anode after an elapse of a certain period of time after said porous contact member is brought into contact with the surface of the seed layer.

41. (Currently Amended) A plating method comprising:

- (a) preparing a substrate having fine recesses for interconnects covered with a seed layer;
- (b) placing a porous member having water retentivity between the surface of the seed layer and an anode spaced from the seed layer at a certain interval; and
- (c) plating the substrate by flowing current between the seed layer and said anode while filling a plating solution between the seed layer and said anode and pressing said porous member against the seed layer under a pressure;
- (d) after said plating the substrate, stopping said flowing current between the seed layer and said anode and then refreshing the plating solution between the seed layer and said anode after separating said porous member from the seed layer; and
- (e) repeating steps (c) and (d).
wherein while said porous member is pressed against the seed layer under a desired pressure, said plating is performed by flowing current between the seed layer and said anode.

42. (Currently Amended) A plating method according to claim 41, wherein said porous member is pressed against the seed layer under a desired pressure, and said porous member and the seed layer are moved relative relatively to each other before performing said plating by flowing current between the seed layer and said anode.

43. (Canceled)

44. (Currently Amended) A plating method comprising:
preparing a substrate having fine recesses for interconnects covered with a seed layer;
placing a porous member having water retentivity between the surface of the seed layer and an anode spaced from the seed layer at a certainan interval; and

filling a plating solution between the seed layer and said anode while immersing said porous member in the plating solution;

removing the plating solution existing in a gap between said porous member and the seed layer by rotating the substrate and said porous member relative to each other while pressing said porous member against the seed layer under pressure; and then

plating the substrate by flowing current between the seed layer and said anode while pressing said porous member against filling a plating solution between the seed layer and said anode; under pressure.

wherein the plating solution existing between said porous member and the seed layer is removed before and after said porous member is pressed against the seed layer under a desired pressure, and then current is flowed between the seed layer and said anode.

45-57. (Canceled)

58. (New) A plating method according to claim 44, wherein said removing the plating solution existing in a gap between said porous member and the seed layer by rotating the substrate and said porous member relative to each other while pressing said porous member against the seed layer under pressure, and said plating the substrate by flowing current between

the seed layer and said anode while pressing said porous member against the seed layer under, are repeated.